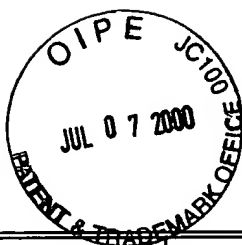


INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. ⁰⁸ 09/921,250
	Applicant(s): Y. INOUE et al.	
	Filing Date: August 29, 1997	Group Art Unit: 1755 1753

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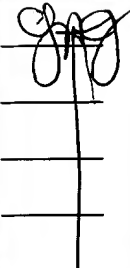
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